MSKSEMI















ESD

TVS

TSS

MOV

GDT

PLED

Broduct data sheet







2. EMITTER **SOT - 23**

3. COLLECTOR

TRANSISTOR (PNP)

FEATURES

- Complementary to MMBT5551-MS
- Ideal for Medium Power Amplification and Switching

MARKING: 2L

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{СВО}	Collector-Base Voltage	-160	V
V _{CEO}	Collector-Emitter Voltage	-150	V
V _{EBO}	Emitter-Base Voltage	-5	V
Ic	Collector Current	-0.6	Α
Pc	Collector Power Dissipation	0.3	W
R _{OJA}	Thermal Resistance from Junction to Ambient	416	°C/W
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55~+150	°

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-100μA, I _E =0	-160			V
Collector-emitter breakdown voltage	V _{(BR)CEO} *	$I_C=-1$ mA, $I_B=0$	-150			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I _E =-10μA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-120V, I _E =0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-4V, I _C =0			-0.1	μA
	h _{FE(1)} *	V _{CE} =-5V, I _C =-1mA	80			
DC current gain	h _{FE(2)} *	V _{CE} =-5V, I _C =-10mA	100		300	
	h _{FE(3)} *	V_{CE} =-5V, I_{C} =-50mA	50			
Collector emitter seturation voltage	V _{CE(sat)1} *	I _C =-10mA, I _B =-1mA			-0.2	V
Collector-emitter saturation voltage	V _{CE(sat)2} *	I _C =-50mA, I _B =-5mA			-0.5	V
Page emitter caturation voltage	V _{BE(sat)1} *	I _C =-10mA, I _B =-1mA			-1	V
Base-emitter saturation voltage	V _{BE(sat)2} *	I _C =-50mA, I _B =-5mA			-1	V
Transition frequency	f⊤	V _{CE} =-5V,I _C =-10mA, f=30MHz	100			MHz

^{*}Pulse test: pulse width ≤300µs, duty cycle≤ 2.0%.

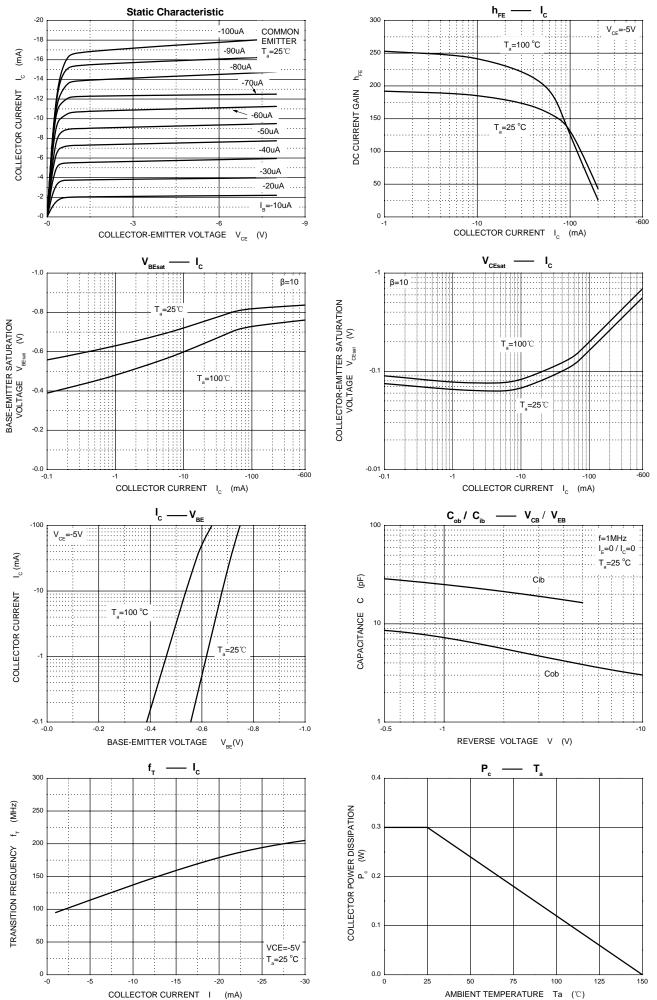
CLASSIFICATION OF h_{FE (2)}

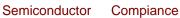
RANK	L	Н
RANGE	100-200	200-300

Semiconductor

Compiance

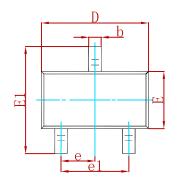
Typical Characteristics

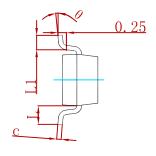


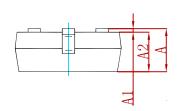




PACKAGE MECHANICAL DATA

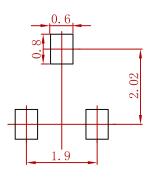






Symbol	Dimensions In Millimeters		Dimensions In Inches		
Зупроі	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
Е	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950) TYP	0.03	7 TYP	
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022	2 REF	
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

Suggested Pad Layout



- 1.Controlling dimension:in millimeters.2.General tolerance:± 0.05mm.3.The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
MMBT5401-MS	SOT-23	3000



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